

KSC2517

High Speed Switching Industrial Use



NPN Epitaxial Silicon Transistor

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	150	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	5	Α
I _{CP}	Collector Current (Pulse)	10	Α
P _C	Collector Dissipation (T _a =25°C)	1.5	W
P _C	Collector Dissipation (T _C =25°C)	30	W
I _B	Base Current	2.5	Α
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

^{*} Pw≤300μs, Duty Cycle≤10%

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 3A$, $I_{B1} = 0.3A$, $L = 1mH$	100		V
V _{CEX} (sus)1	Collector-Emitter Sustaining Voltage	$I_C = 3A$, $I_{B1} = -I_{B2} = 0.3A$ $V_{BE}(off) = -5V$, $L = 180\mu H$, Clamped	150		V
V _{CEX} (sus)2	Collector-Emitter Sustaining Voltage	I_C =6A, I_{B1} = 1.2A, I_{B2} = -0.3A, V_{BE} (off) = -5V, L = 180 μ H, Clamped	100		V
I _{CBO}	Collector Cut-off Current	V _{CB} = 100V, I _E = 0		10	μΑ
I _{CER}	Collector Cut-off Current	$V_{CE} = 100V, R_{BE} = 51\Omega@T_{C} = 125^{\circ}C$		1	mA
I _{CEX1} I _{CEX2}	Collector Cut-off Current	$V_{CE} = 100V, V_{BE}(off) = -1.5V$ $V_{CE} = 100V, V_{BE}(off) = -1.5V$ @ $T_{C} = 125^{\circ}C$		10 1	μA mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 10V, I_{C} = 0$		10	μΑ
h _{FE1} h _{FE2}	* DC Current Gain	$V_{CE} = 5V, I_{C} = 0.2A$ $V_{CE} = 5V, I_{C} = 2A$	40 40	200	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.3A$		0.6	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.3A$		1.5	V
t _{ON}	Turn ON Time	$V_{CC} = 50V, I_{C} = 3A$		0.5	μs
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.3A$		2.5	μs
t _F	Fall Time	$R_L = 17\Omega$		0.5	μs

^{*} Pulse Test: PW≤350μs, Duty Cycle≤2%

\mathbf{h}_{FE} Classification

Classification	R	0	Υ
h _{FE2}	40 ~ 80	60 ~ 120	100 ~ 200

Typical Characteristics

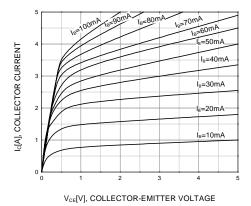


Figure 1. Static Characteristic

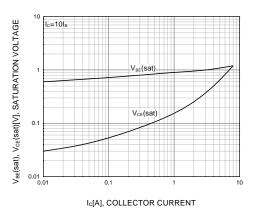


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

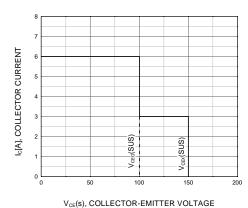


Figure 5. Reverse Bias Safe Operating Area

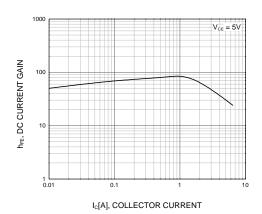


Figure 2. DC current Gain

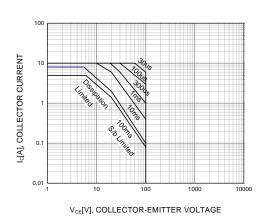


Figure 4. Safe Operating Area

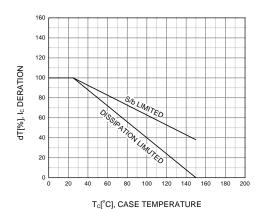


Figure 6. Derating Curve of Safe Operating Areas

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Typical Characteristics (Continued)

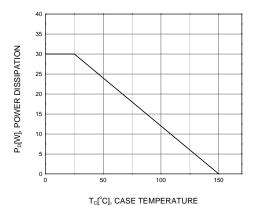
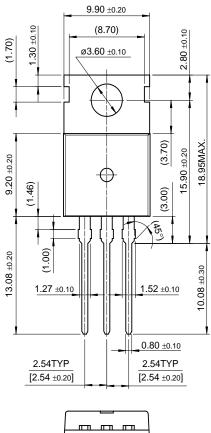


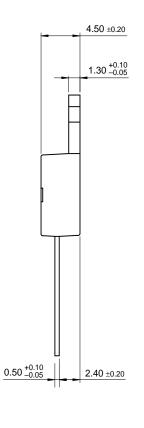
Figure 7. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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